

SANYO	No.4669	2SJ337
		P-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

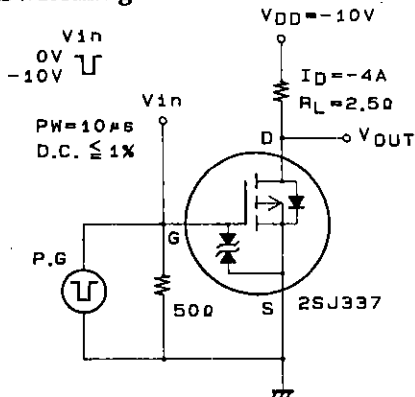
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	-12	V
Gate-to-Source Voltage	V _{GS}	±18	V
Drain Current(DC)	I _D	-8	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	-32 A
Allowable Power Dissipation	P _D	1	W
	P _D	Tc = 25°C	30 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

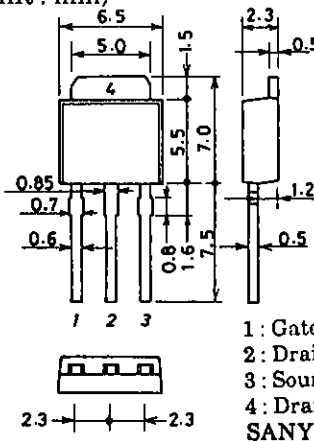
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-12			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±18			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -12V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -4A	4	6		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D = -4A, V _{GS} = -10V		65	90	mΩ
	R _{DS(on)}	I _D = -4A, V _{GS} = -4V		110	150	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10V, f = 1MHz		1000		pF
Output Capacitance	C _{oss}	V _{DS} = -10V, f = 1MHz		900		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -10V, f = 1MHz		220		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		15		ns
Rise Time	t _r	"		50		ns
Turn-OFF Delay Time	t _{d(off)}	"		220		ns
Fall Time	t _f	"		145		ns
Diode Forward Voltage	V _{SD}	I _S = -8A, V _{GS} = 0	-1.0	-1.5		V

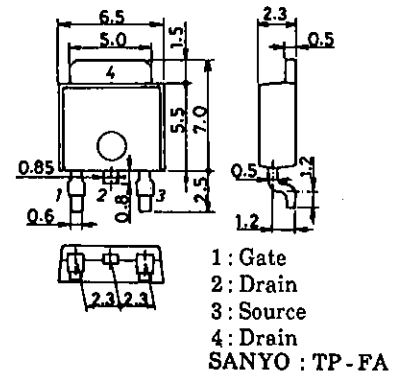
Switching Time Test Circuit

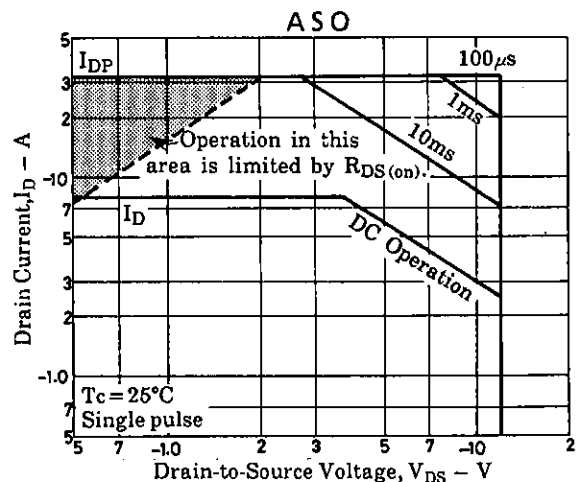
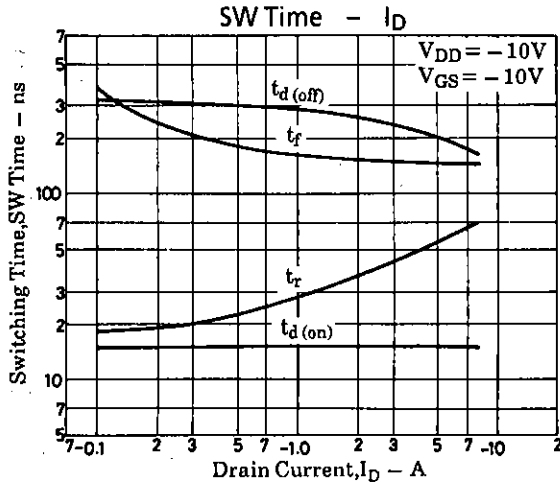
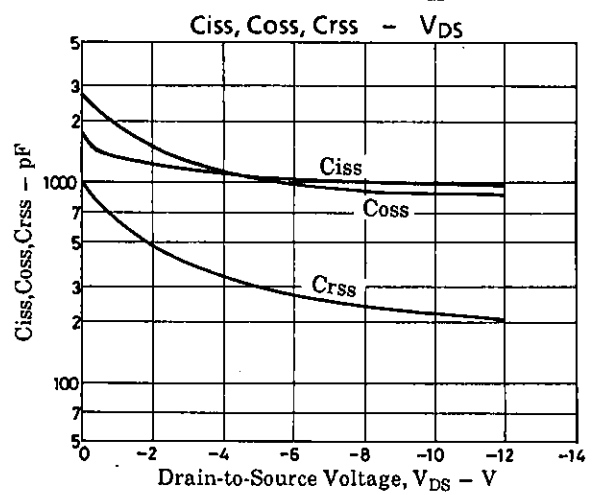
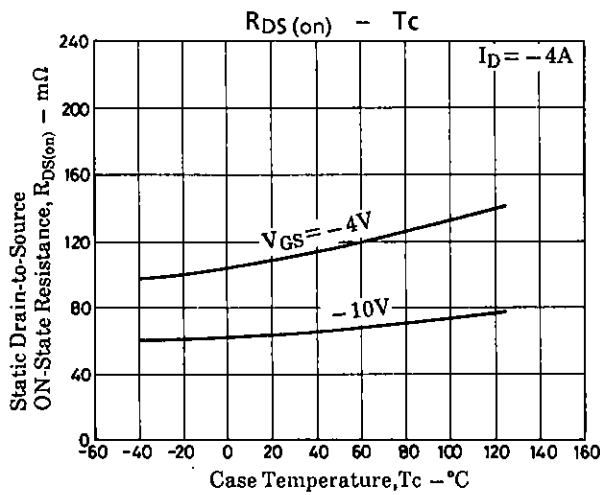
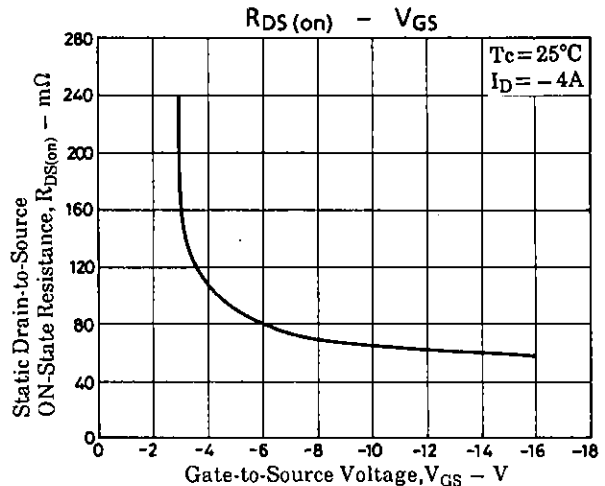
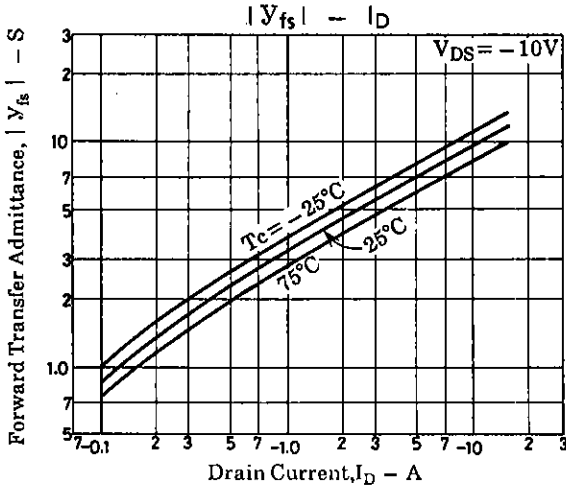
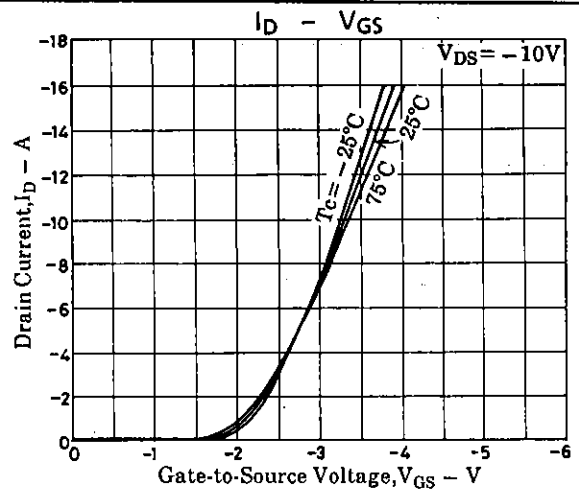
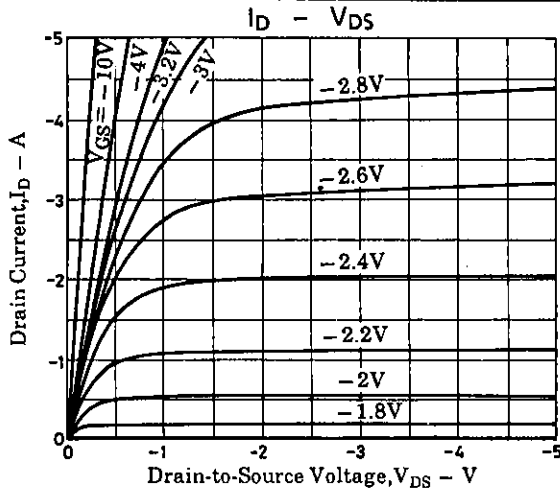


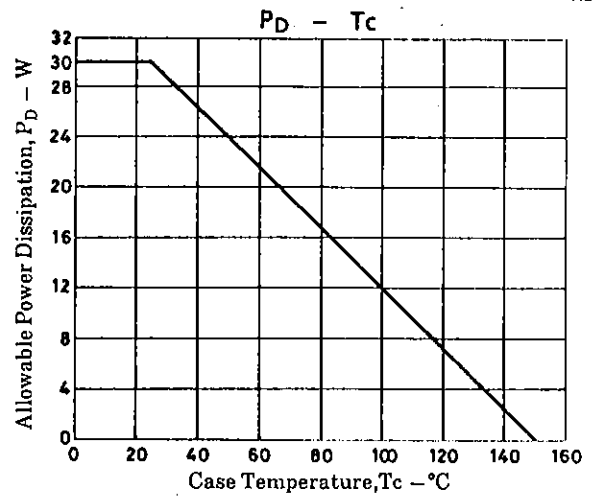
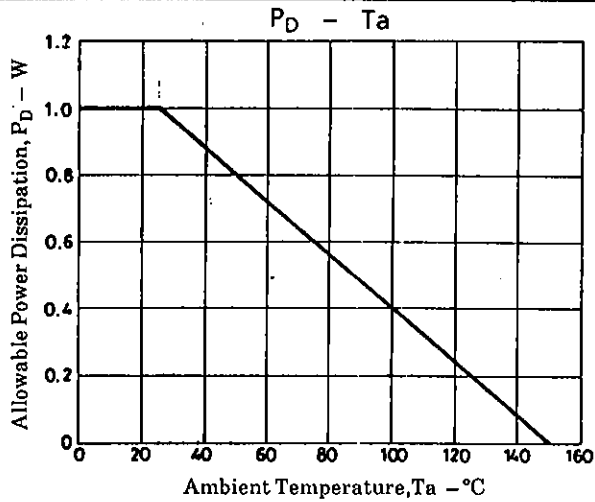
Package Dimensions 2083B (unit : mm)



Package Dimensions 2092B (unit : mm)







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